

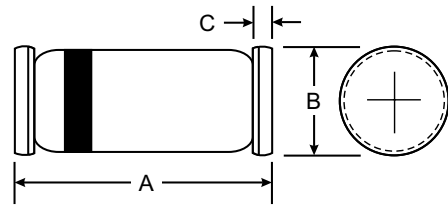


### Features

- Silicon Planar Diode

### Mechanical Data

- Case: SOD-80/LL34
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams
- Marking: Cathode Band Only



LL34/ SOD-80		
Dim	Min	Max
<b>A</b>	3.30	3.70
<b>B</b>	1.30	1.60
<b>C</b>	0.28	0.50
All Dimensions in mm		

### Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Peak reverse voltage, non repetitive		$V_{RSM}$	80	V
Reverse voltage		$V_R$	50	V
Peak forward surge current	$t_p = 1 \mu\text{s}$	$I_{FSM}$	2	A
Repetitive peak forward current		$I_{FRM}$	450	mA
Forward continuous current		$I_F$	200	mA
Power dissipation		$P_V$	500	mW

### Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	on PC board 50 mm x 50 mm x 1.6 mm	$R_{thJA}$	500	K/W
Junction lead	$T_L = \text{constant}$	$R_{thJL}$	350	K/W
Junction temperature		$T_j$	175	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	- 55 to + 175	$^\circ\text{C}$

### Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 50 \text{ mA}$	$V_F$			1100	mV
Reverse current	$V_R = 50 \text{ V}$	$I_R$			1	$\mu\text{A}$
	$V_R = 20 \text{ V}$	$I_R$			50	nA
	$V_R = 20 \text{ V}, T_j = 150^\circ\text{C}$	$I_R$			50	$\mu\text{A}$
Breakdown voltage	$I_R = 100 \mu\text{A}$	$V_{(BR)}$	80			V
Reverse recovery time	$I_F = 10 \text{ mA}, I_R = 10 \text{ mA},$ $i_R = 1 \text{ mA}$	$t_{rr}$			20	ns
Diode capacitance	$V_R = 0, f = 1 \text{ MHz}$	$C_D$			4	pF